LINEAR INTEGRATED CIRCUITS



HIGH-VOLTAGE, HIGH-CURRENT 7 DARLINGTON ARRAYS

These high-voltage, high-current Darlington transistor arrays comprise seven NPN Darlington pairs on a common monolithic substrate. All units feature open collector outputs and integral suppression diodes for inductive loads. Peak currents of 600 mA can be withstood, making them ideal for driving tungsten filament lamps.

The L 201 is a general-purpose array wich may be used with DTL, TTL, PMOS, CMOS, etc. It is pinned with inputs opposite outputs to facilitate circuit board layout and is priced to compete directly with discrete transistor alternatives.

The L 202 was specifically designed for use with 14 to 25V PMOS devices.

Each input has a Zener diode and resistor in series in order to limit the input current to a safe value.

The L203 has a series base resistor to each Darlington pair allowing operation directly with TTL or CMOS operating at a supply voltage of 5V.

The L204 has a series base resistor to each Darlington pair, allowing operation directly with PMOS or CMOS utilizing supply voltage of 6 to 15V.

In all cases, the individual Darlington pair collector current rating is 500 mA. However, outputs may be paralleled for higher load current capability. The devices are supplied in a 16-lead dual in-line plastic package with copper frame.

ABSOLUTE MAXIMUM RATINGS

Vi	Input voltage (for L 202, L 203 and L 204)	30	v
v.	Output voltage (collector-emitter)	50	V
V _{CEO(sus)}	Collector-emitter sustaining voltage	36	v
	Collector current	500	mΑ
I _B	Base current (for L 201 only)	25	mΑ
P _{tot}	Total power dissipation at $T_{amb} = 25^{\circ}C$	1.8	W
T _{op}	Operating junction temperature	-25 to 150	°C
T _{stg}	Storage temperature	-55 to 150	°C

ORDERING NUMBERS: L201B, L203B L202B, L204B

MECHANICAL DATA

Dimensions in mm





CONNECTION DIAGRAM (top view)



SCHEMATIC DIAGRAM

For L 201







For L 202









THERMAL DATA

R _{th j-amb}	Thermal resistance junction-ambient	max.	70	°C/W
nth j-amb	inermal resistance junction-amplent	max.	70	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, unless otherwise specified)

	Parameter	Test conditions	Min.	Typ.	Max.	Unit	Fig. No.
ICEX	Collector cutoff current	for L 201 $V_{CE} = 50V$ for L 202 $V_{CE} = 50V$ V _i = 7V for L 203, L 204 $V_{CE} = 50V$ I _i = 0		0.2 0.2 0.2	3 3 3	μΑ μΑ μΑ	1 2 1
V _{CE(sat)}	Collector-emitter saturation voltage	$I_{C} = 350 \text{ mA}$ $I_{B} = 500 \mu \text{A}$ $I_{C} = 200 \text{ mA}$ $I_{B} = 350 \mu \text{A}$ $I_{C} = 100 \text{ mA}$ $I_{B} = 250 \mu \text{A}$		1.25 1 0.85	1.6 1.3 1.1	v v v	3
l _i	Input current	for L 202 $V_i = 17V$ for L 203 $V_i = 3.85V$ for L 204 $V_i = 5V$ $V_i = 12V$		0.75 0.9 0.35 1.1	1.3 1.35 0.5 1.45	mA mA mA mA	5
I _{C(off)}		V _{CE} = 50V Ι _i = 25 μA	2		25	μA	4
V _i	Input voltage			10.5 1.8 1.7 4.5 5	13 3 2.4 6 8		7
h _{FE}	DC current gain (for L 201 only)	I _C = 350 mA V _{CE} = 2V	1000	3000			3
I _R	Parallel diode reverse current	V _R = 50V		0.5	50	μA	6
VF	Parallel diode forward voltage	i _F = 350 mA		1.4	2	v	8
t _{PLH}	Turn-on delay time	0.5 V _i to 0.5 V _o			5	μs	-
t _{PHL}	Turn-off delay time	0.5 V _i to 0.5 V _o			5	μs	-



TEST CIRCUITS

Fig 1 - For L 201, L 203 and L 204



Fig. 4 - For L 201, L 202, L 203 and L 204



Fig. 2 - For L 202



Fig. 3 - For L 201, L 202, L 203 and L 204



Fig. 5 - For L 202, L 203, and L 204

Fig. 6 - For L 201, L 202, L 203 and L 204





Fig. 7 - For L 202, L 203, and L 204



Fig. 8 - For L 201, L 202, L 203 and L 204





APPLICATION CIRCUITS

PMOS to load (L 202 and L 204)



Fig. 9 - DC current gain. vs. collector current (for L 201)



Fig. 12 - Input current vs. input voltage (for L 202 and L 204)



Buffer for high current load (L 203 and L 204)



Fig. 10 - Collector current vs. collector emitter saturation voltage



Fig. 13 - Input current vs. input voltage (L 203)



TTL to load (L 203)



Fig. 11 – Peak collector current as a function fo duty cycle and number of outputs



Fig. 14 - Power rating chart

